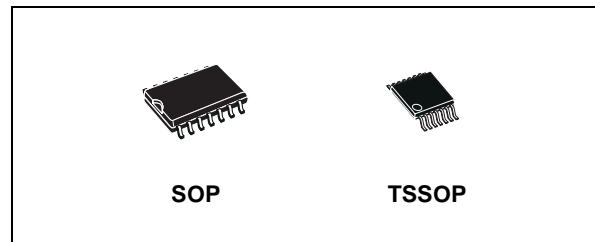


LOW VOLTAGE CMOS HEX SCHMITT INVERTER

- HIGH SPEED:
 $t_{PD} = 6 \text{ ns (TYP.) at } V_{CC} = 3.3 \text{ V}$
- HYSTERESIS INPUT VOLTAGE:
 $V_H = 650\text{mV (TYP.) at } V_{CC} = 3.0 \text{ V}$
- COMPATIBLE WITH TTL OUTPUTS
- LOW POWER DISSIPATION:
 $I_{CC} = 2\mu\text{A(MAX.) at } T_A=25^\circ\text{C}$
- LOW NOISE:
 $V_{OLP} = 0.3\text{V (TYP.) at } V_{CC} = 3.3\text{V}$
- 75Ω TRANSMISSION LINE DRIVING CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 12\text{mA (MIN) at } V_{CC} = 3.0 \text{ V}$
- PCI BUS LEVELS GUARANTEED AT 24 mA
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC(OPR)} = 2\text{V to } 3.6\text{V}$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 14
- IMPROVED LATCH-UP IMMUNITY



ORDER CODES

PACKAGE	TUBE	T & R
SOP	74LVQ14M	74LVQ14MTR
TSSOP		74LVQ14TTR

including buffer output, which enables high noise immunity and stable output.

Pin configuration and function are the same as those of the 74LVQ04 but the 74LVQ14 has hysteresis between the positive and negative input threshold typically of 650mV.

This together with its schmitt trigger function allows it to be used on line receivers with slow rise/fall input signals.

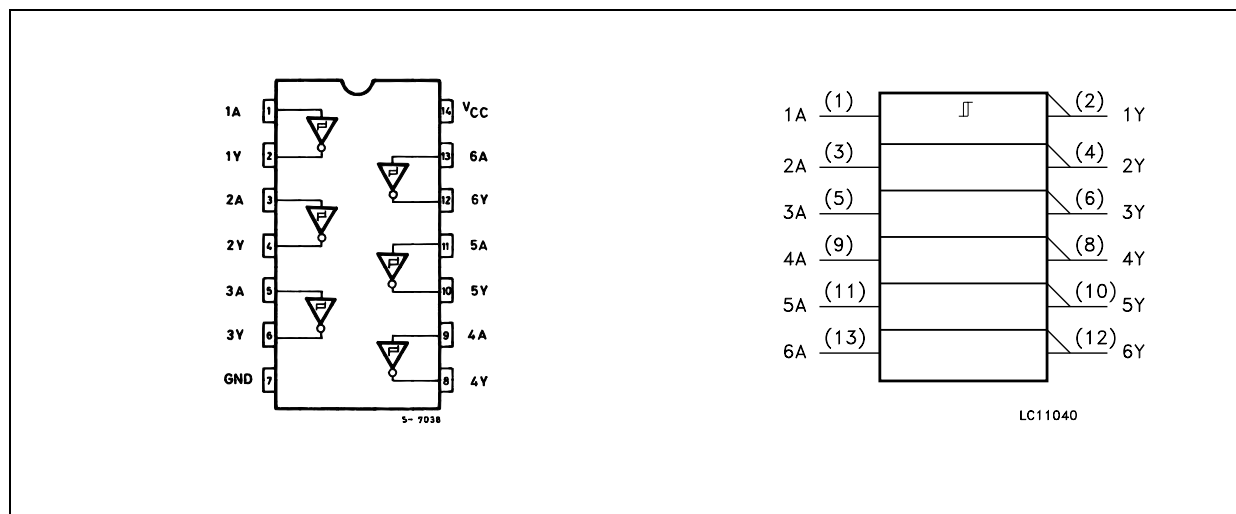
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

DESCRIPTION

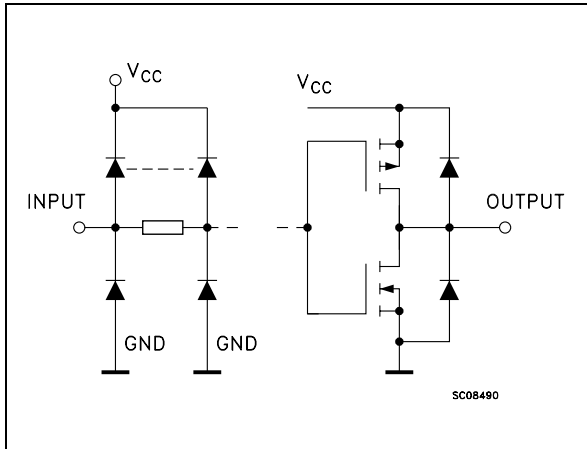
The 74LVQ14 is a low voltage CMOS HEX SCHMITT INVERTER fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is ideal for low power and low noise 3.3V applications.

The internal circuit is composed of 3 stages

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	Y
L	H
H	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 50	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 300	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage (note 1)	2 to 3.6	V
V _I	Input Voltage	0 to V _{CC}	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C

1) Truth Table guaranteed: 1.2V to 3.6V

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{t+}	Positive Input Threshold	3.0				2.2		2.2		2.2	V
V _{t-}	Negative Input Threshold	3.0		0.5			0.5		0.5		V
V _H	Hysteresis Voltage	3.0		0.3		1.2	0.3	1.2	0.3	1.2	V
V _{OH}	High Level Output Voltage	3.0	I _O =-50 μA	2.9	2.99		2.9		2.9		V
			I _O =-12 mA	2.58			2.48		2.48		
			I _O =-24 mA				2.2		2.2		
V _{OL}	Low Level Output Voltage	3.0	I _O =50 μA		0.002	0.1		0.1		0.1	V
			I _O =12 mA		0	0.36		0.44		0.44	
			I _O =24 mA					0.55		0.55	
I _I	Input Leakage Current	3.6	V _I = V _{CC} or GND			± 0.1		± 1		± 1	μA
I _{CC}	Quiescent Supply Current	3.6	V _I = V _{CC} or GND			2		20		20	μA
I _{OLD}	Dynamic Output Current (note 1, 2)	3.6	V _{OLD} = 0.8 V max				36		25		mA
I _{OHD}			V _{OHD} = 2 V min				-25		-25		mA

1) Maximum test duration 2ms, one output loaded at time

2) Incident wave switching is guaranteed on transmission lines with impedances as low as 75Ω

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	3.3	C _L = 50 pF		0.3	0.8					V
V _{OLV}				-0.8	-0.3						
V _{IHD}	Dynamic High Voltage Input (note 1, 3)	3.3		2							V
V _{ILD}	Dynamic Low Voltage Input (note 1, 3)	3.3					0.8				

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

74LVQ14

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, $R_L = 500 \Omega$, Input $t_r = t_f = 3 \text{ ns}$)

Symbol	Parameter	Test Condition		Value						Unit	
		V_{CC} (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t_{PLH} t_{PHL}	Propagation Delay Time	2.7			7.0	11.0		13.0		15.0	ns
		3.3(*)			6.0	9.0		10.5		12.0	
t_{OSLH} t_{OSHL}	Output To Output Skew Time (note1, 2)	2.7			0.5	1.0		1.0		1.0	ns
		3.3(*)			0.5	1.0		1.0		1.0	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$)

2) Parameter guaranteed by design

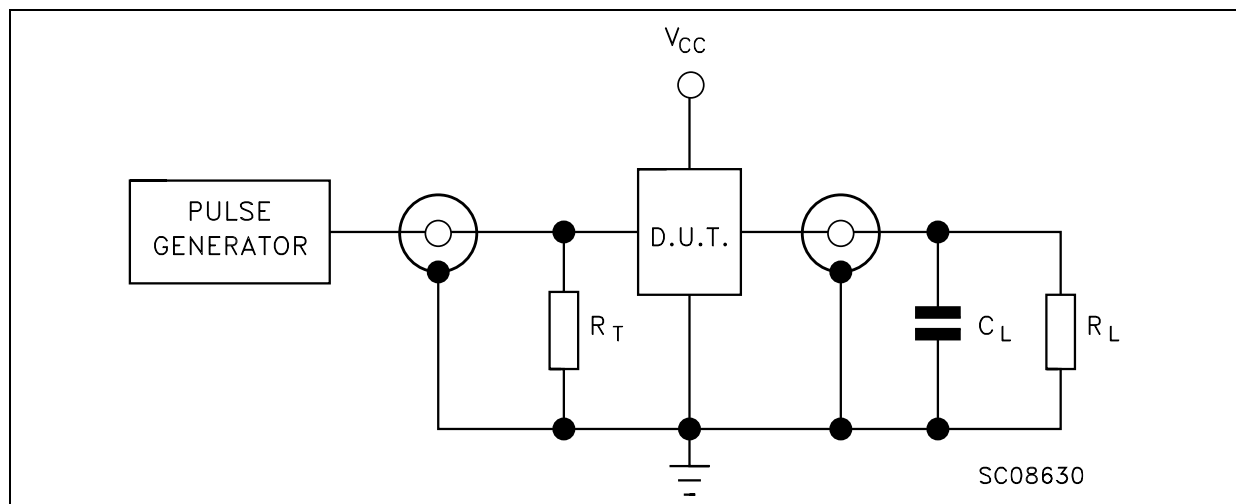
(*) Voltage range is $3.3\text{V} \pm 0.3\text{V}$

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V_{CC} (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C_{IN}	Input Capacitance	3.3			4						pF
C_{PD}	Power Dissipation Capacitance (note 1)	3.3	$f_{IN} = 10\text{MHz}$		29						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/6$ (per gate)

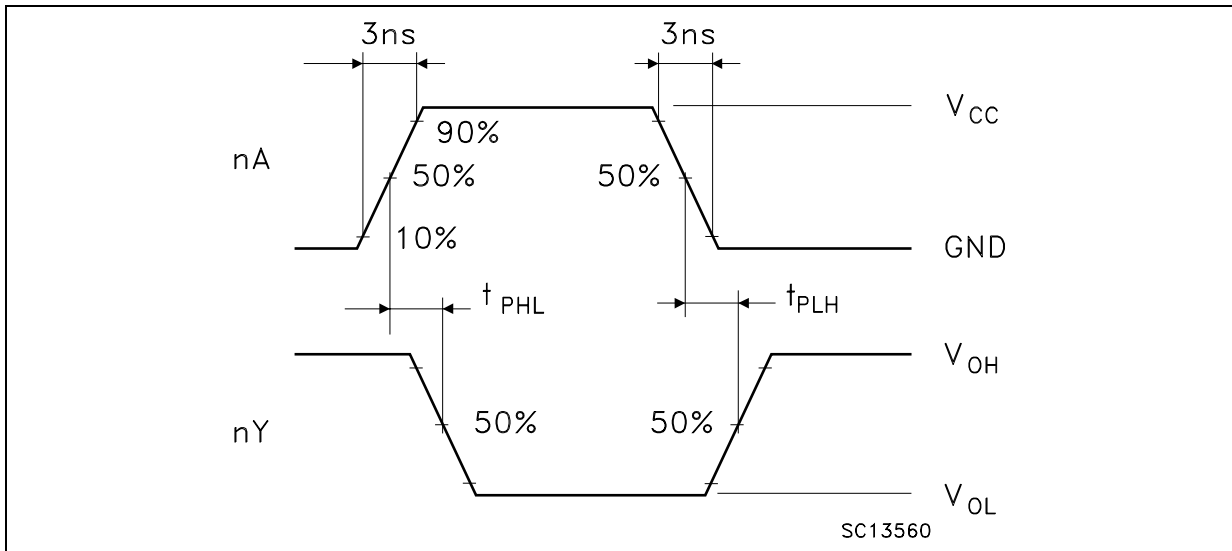
TEST CIRCUIT



$C_L = 50\text{pF}$ or equivalent (includes jig and probe capacitance)

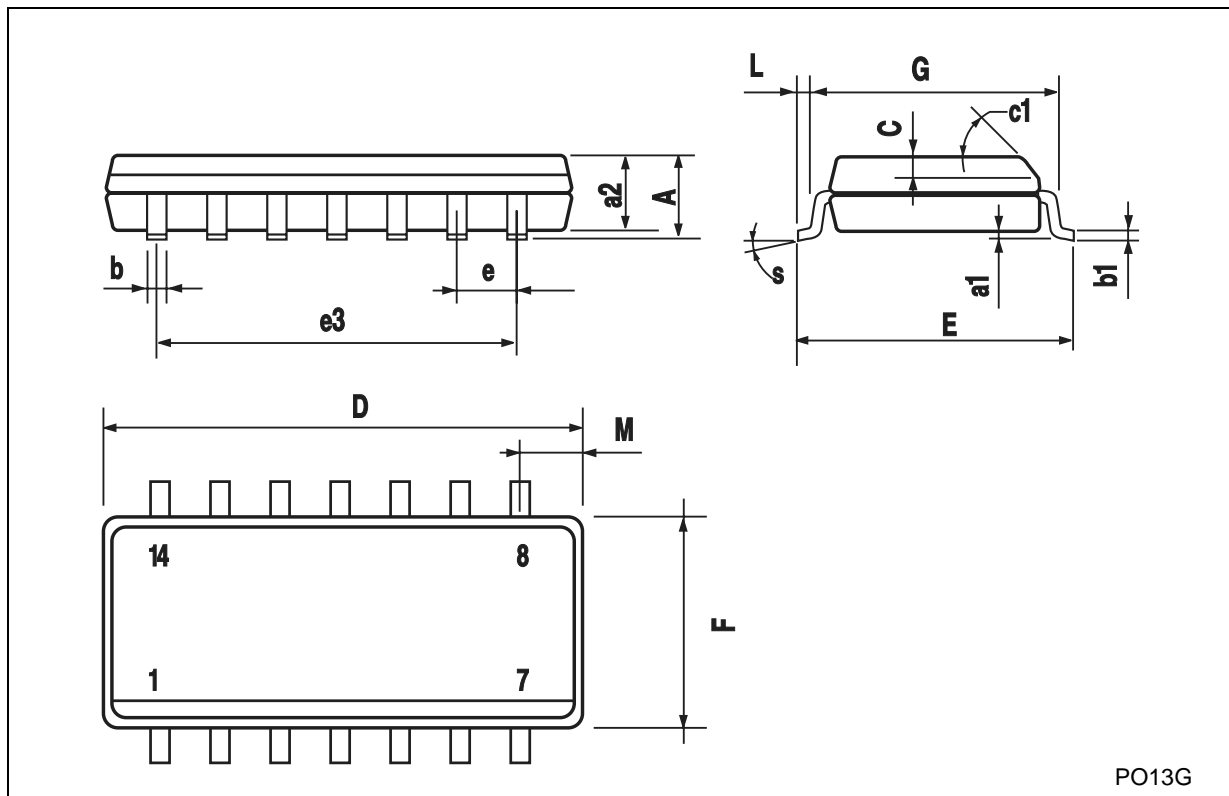
$R_L = 500\Omega$ or equivalent

$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)

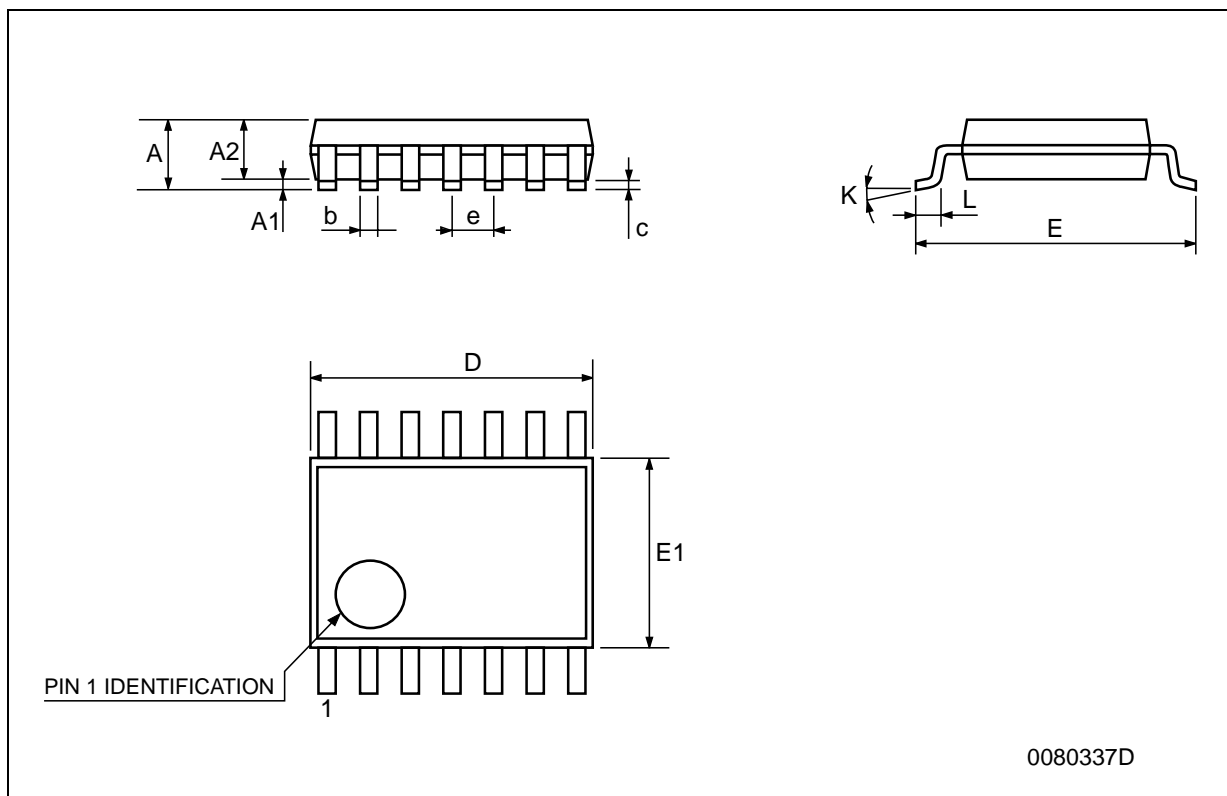
SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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